

High Speed Infrared Emitting Diode, 850 nm, Surface Emitter Technology



DESCRIPTION

As part of the [SurfLight™](#) portfolio, the reVSMY2853SL is an infrared, 850 nm, side looking emitting diode based on GaAlAs surface emitter chip technology with extreme high radiant intensities, high optical power and high speed, molded in clear, untinted plastic packages (with lens) for surface mounting (SMD).

APPLICATIONS

- IrDA compatible data transmission
- Miniature light barrier
- Photointerrupters
- Optical switch
- Emitter source for proximity sensors
- IR touch panels
- IR illumination
- 3D TV

FEATURES

- Package type: surface mount
- Package form: side view
- Dimensions (L x W x H in mm): 2.3 x 2.55 x 2.3
- Peak wavelength: $\lambda_p = 850$ nm
- High reliability
- High radiant power
- Very high radiant intensity
- Angle of half intensity: $\phi = \pm 28^\circ$
- Suitable for high pulse current operation
- Package matches with detector VEMD2xx3SLX01 and VEMT2xx3SLX01 series
- Floor life: 4 weeks, MSL 2a, acc. J-STD-020
- Material categorization: For definitions of compliance please see www.vishay.com/doc?99912



PRODUCT SUMMARY

COMPONENT	I_e (mW/sr)	ϕ (deg)	λ_p (nm)	t_r (ns)
VSMY2853SL	35	± 28	850	10

Note

- Test conditions see table “Basic Characteristics“

ORDERING INFORMATION

ORDERING CODE	PACKAGING	REMARKS	PACKAGE FORM
VSMY2853SL	Tape and reel	MOQ: 3000 pcs, 3000 pcs/reel	Side view

Note

- MOQ: minimum order quantity

ABSOLUTE MAXIMUM RATINGS ($T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified)				
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
Reverse voltage		V_R	5	V
Forward current		I_F	100	mA
Peak forward current	$t_p/T = 0.5$, $t_p = 100\text{ }\mu\text{s}$	I_{FM}	200	mA
Surge forward current	$t_p = 100\text{ }\mu\text{s}$	I_{FSM}	1	A
Power dissipation		P_V	190	mW
Junction temperature		T_j	100	$^{\circ}\text{C}$
Operating temperature range		T_{amb}	- 40 to + 85	$^{\circ}\text{C}$
Storage temperature range		T_{stg}	- 40 to + 100	$^{\circ}\text{C}$
Soldering temperature	acc. figure 7, J-STD-020	T_{sd}	260	$^{\circ}\text{C}$
Thermal resistance junction/ambient	J-STD-051, soldered on PCB	R_{thJA}	250	K/W

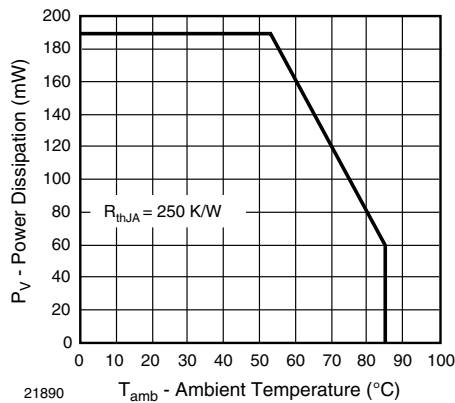


Fig. 1 - Power Dissipation Limit vs. Ambient Temperature

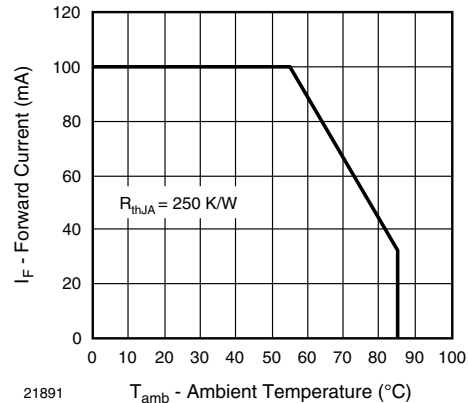


Fig. 2 - Forward Current Limit vs. Ambient Temperature

BASIC CHARACTERISTICS ($T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified)						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Forward voltage	$I_F = 100\text{ mA}$, $t_p = 20\text{ ms}$	V_F		1.65	1.9	V
	$I_F = 1\text{ A}$, $t_p = 100\text{ }\mu\text{s}$	V_F		2.9		V
Temperature coefficient of V_F	$I_F = 1\text{ mA}$	TK_{V_F}		- 1.45		mV/K
	$I_F = 10\text{ mA}$	TK_{V_F}		- 1.3		mV/K
Reverse current		I_R	not designed for reverse operation			μA
Junction capacitance	$V_R = 0\text{ V}$, $f = 1\text{ MHz}$, $E = 0\text{ mW/cm}^2$	C_J		125		pF
Radiant intensity	$I_F = 100\text{ mA}$, $t_p = 20\text{ ms}$	I_e	20	35	50	mW/sr
	$I_F = 1\text{ A}$, $t_p = 100\text{ }\mu\text{s}$	I_e		300		mW/sr
Radiant power	$I_F = 100\text{ mA}$, $t_p = 20\text{ ms}$	ϕ_e		55		mW
Temperature coefficient of radiant power	$I_F = 100\text{ mA}$	TK_{ϕ_e}		- 0.35		%/K
Angle of half intensity		ϕ		± 28		deg
Peak wavelength	$I_F = 100\text{ mA}$	λ_p	840	850	870	nm
Spectral bandwidth	$I_F = 30\text{ mA}$	$\Delta\lambda$		30		nm
Temperature coefficient of λ_p	$I_F = 30\text{ mA}$	TK_{λ_p}		0.25		nm/K
Rise time	$I_F = 100\text{ mA}$, 20 % to 80 %	t_r		10		ns
Fall time	$I_F = 100\text{ mA}$, 20 % to 80 %	t_f		10		ns

BASIC CHARACTERISTICS ($T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified)

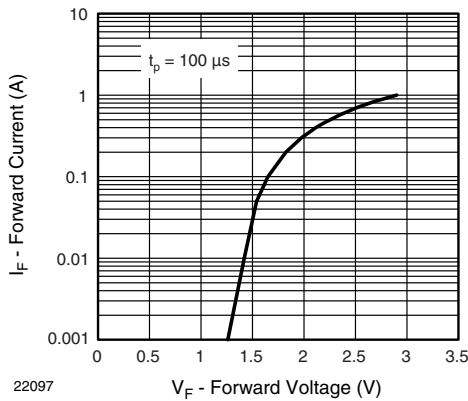


Fig. 3 - Forward Current vs. Forward Voltage

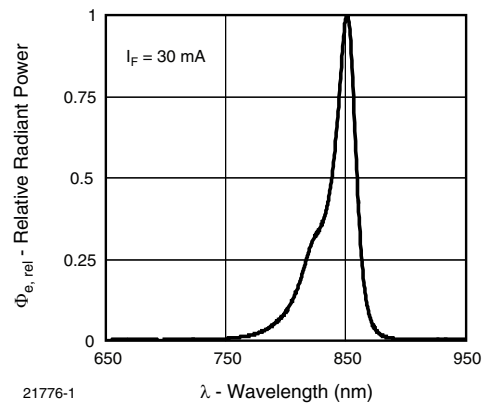


Fig. 5 - Relative Radiant Power vs. Wavelength

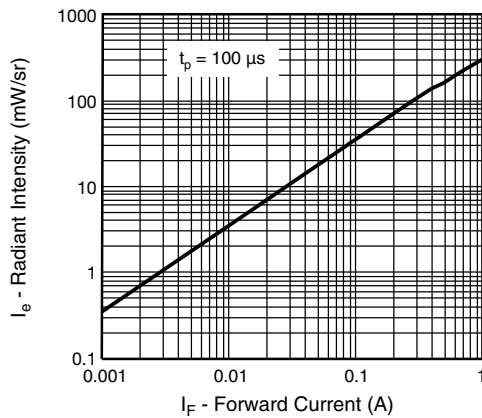


Fig. 4 - Radiant Intensity vs. Forward Current

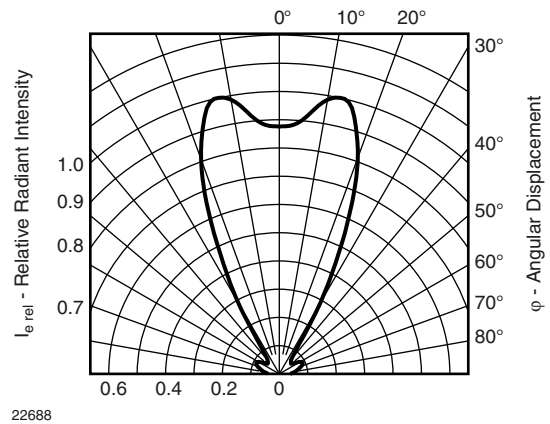


Fig. 6 - Relative Radiant Intensity vs. Angular Displacement

SOLDER PROFILE

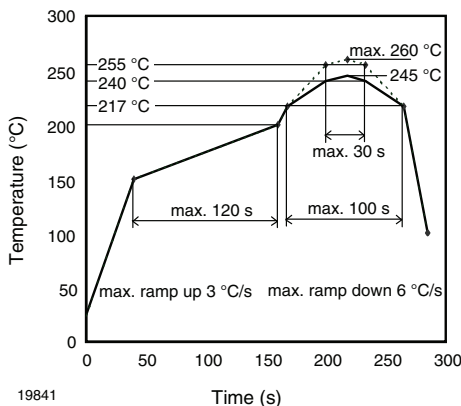


Fig. 7 - Lead (Pb)-free Reflow Solder Profile acc. J-STD-020

DRYPACK

Devices are packed in moisture barrier bags (MBB) to prevent the products from moisture absorption during transportation and storage. Each bag contains a desiccant.

FLOOR LIFE

Floor life (time between soldering and removing from MBB) must not exceed the time indicated on MBB label:

Floor life: 4 weeks

Conditions: $T_{amb} < 30\text{ }^{\circ}\text{C}$, $\text{RH} < 60\%$

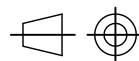
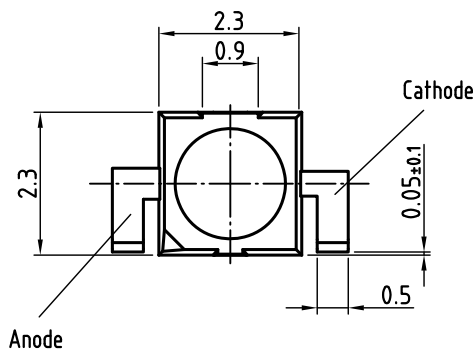
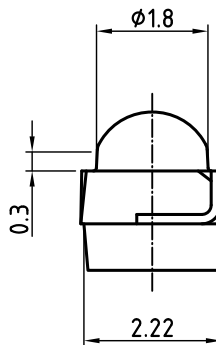
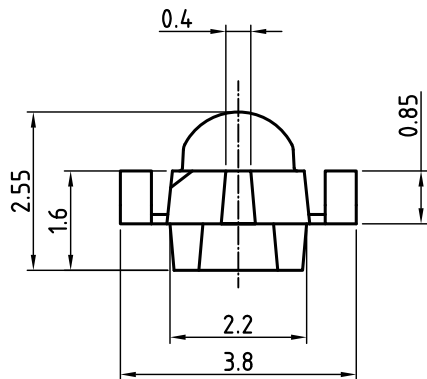
Moisture sensitivity level 2a, acc. to J-STD-020.

DRYING

In case of moisture absorption devices should be baked before soldering. Conditions see J-STD-020 or label. Devices taped on reel dry using recommended conditions 192 h at $40\text{ }^{\circ}\text{C}$ (+ $5\text{ }^{\circ}\text{C}$), $\text{RH} < 5\%$.



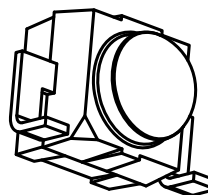
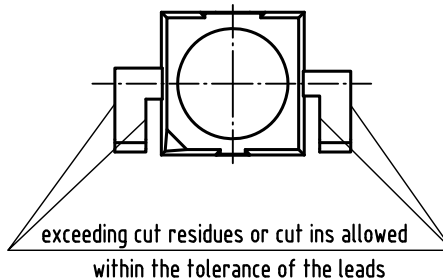
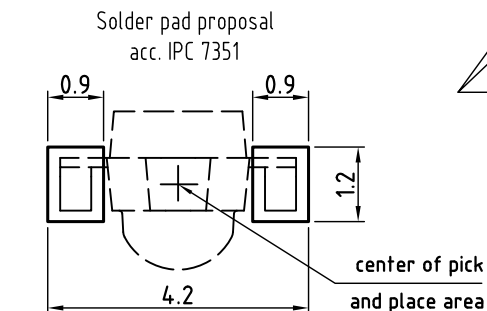
PACKAGE DIMENSIONS in millimeters: VSMY2853SL



technical drawings according to DIN specifications

Dimensions in mm

Not indicated tolerances ±0.2

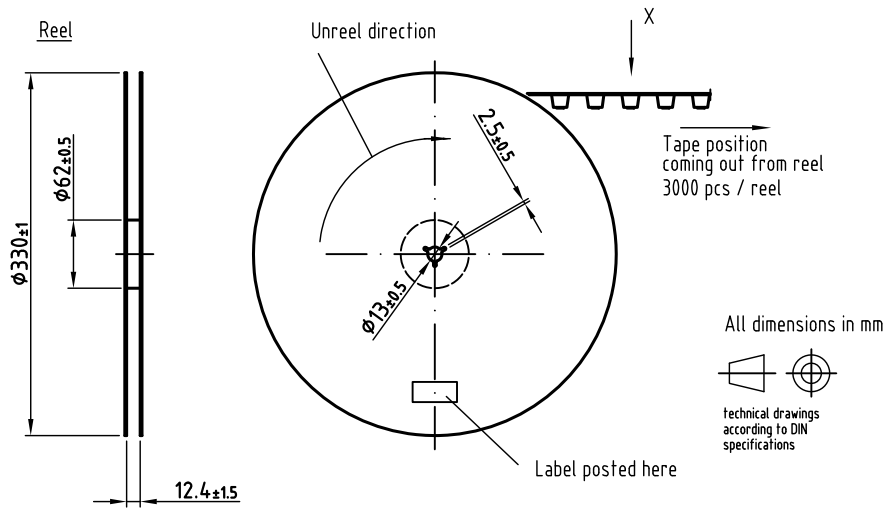


Drawing refers to following types: VSMY2853SL

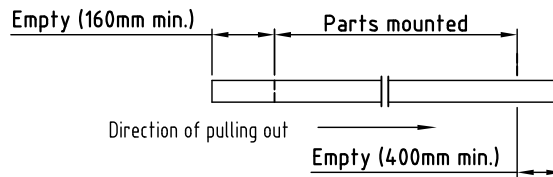
Drawing-No.: 6.544-5410.03-4

Issue: prel. 03.08.12

TAPING AND REEL DIMENSIONS in millimeters: **VSMY2853SL**

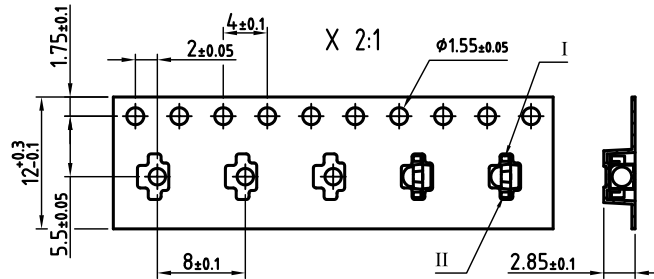


Leader and trailer tape:



Terminal position in tape

Device	Lead I	Lead II
V SMB294.3SLX01	Cathode	Anode
V SMF2893SLX01		
V SMB294.8SL		
V EMD2023SLX01	Collector	Emitter
V EMD2523SLX01		
V EMT2023SLX01	Anode	Cathode
V EMT2523SLX01		
V SMY2853SL	Anode	Cathode



Drawing refers to following types: see table
Reel dimensions and tape

Drawing-No.: 9.800-5123.01-4
Issue: prel; 01.02.13